

**AMENDMENT TO THE CLAIMS**

1. (Currently amended) A semiconductor device comprising:

a gate insulating film having a multilayer structure including a zirconium oxide film and a high dielectric constant film which is a hafnium oxide film or a hafnium aluminate film and which is formed on the zirconium oxide film,

wherein a silicon nitride film is formed under the zirconium oxide film,

the high dielectric constant film contains nitrogen,

[[the]] an interface layer between the silicon nitride film and the zirconium oxide film is formed of a zirconium silicate film.

2-22. (Canceled)

23. (Previously presented) The semiconductor device of claim 1, wherein the silicon nitride film has a thickness of 1 nm or less.

24. (Previously presented) The semiconductor device of claim 1, further comprising a gate electrode on the gate insulating film.

25. (Previously presented) The semiconductor device of claim 24, wherein the gate electrode is a titanium nitride film.

26. (Previously presented) The semiconductor device of claim 24, wherein the gate electrode has a thickness of not less than 30 nm and not more than 100 nm.

27. (Previously presented) The semiconductor device of claim 24, further comprising an insulating sidewall spacer formed to cover the side faces of the gate electrode.

28-34. (Cancelled)

35. (Previously presented) The semiconductor device of claim 1, wherein the high dielectric constant film directly contacts the top surface of the zirconium oxide film.

36-40. (Cancelled)